

Abstract

Method for producing electric conductive structures for use in high frequency technology

A method is specified for producing electric conductive structures
5 for use in high frequency technology on a conductive structure
carrier with layer spacings significantly less than 180 μm , e.g. 30
 μm , using microstrip conductors. In accordance with this method a
combination of a laser structuring method with an etching method in
conjunction with a resist is used, which at least as regards the
10 lasering with the laser structuring method, the etching with the
etching method and the minimum thickness with which it can be
applied to the conductive structure carrier, has properties which at
least correspond to those of chemical tin or of an amorphous resist.

Figure 1